

Quasiparticle band structures and optical properties of strained monolayer MoS₂ and WS₂

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The quasiparticle (QP) band structures of both strainless and strained monolayer MoS₂ are investigated using more accurate many body perturbation *GW* theory and maximally localized Wannier functions (MLWFs) approach. For the strainless state, the partially self-consistent *GW*₀ (sc*GW*₀) calculation demonstrates that monolayer MoS₂ is a direct semiconductor, consistent with recent experimental observations. By solving the Bethe-Salpeter equation (BSE) including excitonic effects, the predicted optical gap magnitude is consistent with available experimental data. We further predict that the strong exciton binding energy is in the range of 0.50–0.40 eV and also is nearly unchanged with increasing strain. In addition, the sc*GW*₀ calculations also predict that monolayer MoS₂ maintains its direct characteristic under the tensile strain up to 1.41%. As the tensile strain increases further, the electron effective mass decreases, the covalent bonding weakens, and a direct to indirect gap transition occurs. The sc*GW*₀ and BSE calculations are also performed on monolayer WS₂, similar characteristics are predicted and WS₂ possesses the lightest effective mass at the same strain among monolayers Mo(S,Se) and W(S,Se). The present calculation results suggest a viable route to tune the electronic properties of monolayer transition-metal dichalcogenides (TMDs) using strain engineering for potential applications in high performance electronic devices.

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I. INTRODUCTION

Bulk TMDs consisting of two dimensional (2D) sheets bound to each other through weak van der Waals forces have been studied extensively owing to their potential applications in photocatalysis [1] and catalysis [2, 3]. MoS₂, WS₂, MoSe₂, and WSe₂ are examples of such TMDs. Recently, their 2D monolayer counterparts were successfully fabricated using micromechanical cleavage method [4]. Since then, these monolayer materials have attracted significant attention [5–13].

For monolayer MoS₂, a strong photoluminescence (PL) peak at about 1.90 eV, together with peaks at about 1.90 and 2.05 eV of the adsorption spectrum indicated that MoS₂ undergoes an indirect to direct band gap transition when its bulk or multilayers form is replaced by a monolayer [6–8]. Theoretical studies employed density functional theory (DFT) method also predicted monolayer MoS₂ to have a direct gap of 1.78 eV [5]. It is known however that DFT does not describe excited state of solids reliably. Furthermore, an important character in low-dimensional systems is their strong exciton binding due to the weak screening compared to bulk cases. Therefore, the good band gap agreement between theoretical and experimental results for monolayer MoS₂ may be a mere coincidence. DFT calculations also showed that the band gap of monolayer MoS₂ was sensitively dependent

on strain [10–12], and the direct to indirect band gap transition was predicted at tensile strain of 0.3% [10], while others reported at 1% [13]. Furthermore, shifts of PL peak for the monolayer MoS₂ were also observed experimentally, which was attributed to the strain introduced by covered oxides [14]. In order to address above questions, it is important and necessary to employ more accurate calculation method beyond DFT to investigate the electronic structures of strained monolayer MoS₂.

The most common method to circumvent drawback of DFT is the *GW* approximation [15], in which, self-energy operator Σ contains all the electron-electron exchange and correlation effects. The sc*GW*₀ approach, in which only the orbitals and eigenvalues in *G* are iterated, while *W* is fixed to the initial DFT *W*₀, was shown to be more accurate in many cases to predict band gaps of solids [16]. The off-diagonal components of the self-energy Σ should be included in sc*GW*₀ calculations, since this inclusion has been proved particularly useful for materials such as NiO and MnO [17]. It is noted that Σ within *GW* approximation is defined only on a uniform *k* mesh in Brillouin-zone, due to its non-locality. Therefore, unlike DFT band structure plot, the QP eigenvalues at arbitrary *k* points along high symmetry lines cannot be performed directly [18]. Started from the sc*GW*₀ calculation, the QP band structure can be interpolated using MLWFs approach. This combination was demonstrated to be accurate and efficient for the sc*GW* band structure [18]. The *GW* results were shown to agree well with the photoemission data [19], while in order to reproduce the experimental adsorption spectra, the consideration of attraction between quasi-electron and quasi-hole (on top of *GW* approximation) by solving BSE is indispensable

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[19], particularly for the low-dimensional systems with strong excitonic effect. The main goal of this study is to accurately predict the QP band structures and optical spectra of monolayer MoS₂ as a function of strain by adopting the DFT-sc GW_0 -BSE approach.

Strain in monolayer MoS₂ can be produced either by epitaxy on a substrate or by mechanical loading. It is well-known that strain can be used to tune the electronic properties of materials. This is particularly important for two-dimensional materials, which can sustain a large tensile strain. In fact, shifts of PL peak observed experimentally in monolayer MoS₂ was attributed to strain [14], and the magnetic properties of MoS₂ nanoribbons could be tuned by applying strain [20].

By adopting the aforementioned approach, we systematically investigate how the electronic structures and optical properties of monolayer MoS₂ evolve as a function of strain. Based on the more accurate band structures, the effective masses of carriers are calculated. In addition, this calculation approach is also employed to investigate other monolayer TMDs, that is, WS₂, MoSe₂, and WSe₂.

II. DETAILS OF CALCULATION

Our DFT calculations were performed by adopting the generalized gradient approximation (GGA) of PBE functional [21] for the exchange correlation potential and the projector augmented wave (PAW) [22] method as implemented in the Vienna ab initio simulation package [23]. 12 valence electrons are included for both Mo and W pseudopotentials. The electron wave function was expanded in a plane wave basis set with an energy cutoff of 600 eV. A vacuum slab more than 15 Å is added in the direction normal to the nanosheet plane. For the Brillouin zone integration, a $12 \times 12 \times 1$ Γ centered Monkhorst-Pack k -point mesh is used. In the following GW QP calculations, both single-shot G_0W_0 and more accurate partially sc GW_0 calculations are performed. 184 empty conduction bands are included. The energy cutoff for the response function is set to be 300 eV, the obtained band gap value is almost identical to the case of 400 eV. The convergence of our calculations has been checked carefully. For the Wannier band structure interpolation, d orbitals of Mo (W) and p orbitals of S (Se) are chosen for initial projections. Our BSE spectrum calculations are carried out on top of sc GW_0 . The six highest valence bands and the eight lowest conduction bands were included as basis for the excitonic state. BSE was solved using the Tamm-Dancoff approximation. Notice that the applied strain in the present study is all equibiaxial, unless stated otherwise.

III. RESULTS AND DISCUSSIONS

We first analyze the density of states (DOS) for monolayer MoS₂. The d orbitals of Mo and p orbitals of S con-

tribute most to the states around the band gap, similar to previous studies [10–12]. Fig. 1 shows the projected d orbitals of Mo and p orbitals of S as well as the decomposed d orbitals for monolayer MoS₂ at the experimental lattice of 3.160 Å for bulk MoS₂ [10] (Fig. 1(a) and (b)) and under 3% tensile strain (Fig. 1(c) and (d)), respectively. Based on the DOS, the d orbitals of Mo and p orbitals of S are chosen as the initial projections in the Wannier interpolated method. Fig. 2 shows the identical DFT band structures of monolayer MoS₂ obtained by the non-selfconsistent (Non-Scf) calculation at fixed potential and Wannier interpolation method, respectively, confirming that our choice of the initial projections and inner window energy is appropriate. Based on the good results for monolayer MoS₂, the same procedure is also employed for remaining monolayer TMDs.

A. QP band structures of strained monolayer MoS₂

The QP band structures of monolayer MoS₂ at four lattice constants of 3.160, 3.190 (the optimized value from the present work), 3.255, and 3.350 Å are plotted in Fig. 3, corresponding to 0%, 1%, 3%, and 6% tensile strains (with reference to 3.160 Å), respectively. As shown in Fig. 3(a), the band structure obtained by DFT for strainless MoS₂ is a direct band gap semiconductor with a band gap energy of 1.78 eV, while the indirect band gap of 2.49 eV is predicted by G_0W_0 , which is consistent well with Olsen's results [9]. Obviously this G_0W_0 indirect band gap is contrary to the PL observations [6–8]. The QP band structures predicted by our sc GW_0 calculation show that MoS₂ is a K to K direct band gap semiconductor with a band gap energy of 2.80 eV. This prediction is in excellent agreement with the recent calculation for MoS₂ at the experimental lattice using full-potential linearized muffin-tin-orbital method (FP-LMTO) [24], which predicted a K to K direct band gap of 2.76 eV.

It should be noted that in the 2D materials, the excitonic effect is strong due to the weak screening. Thus it is important to consider the attraction between the quasi-electron and quasi-hole by solving the BSE discussed below in order to make the predicted optical gap consistent with the optical spectra.

Fig. 3(b) shows the band structure of monolayer MoS₂ at 3.190 Å corresponding to 1% strain. The DFT result predicts the monolayer MoS₂ to be an indirect band gap with K to Γ of 1.67 eV. Previous DFT studies also found that monolayer MoS₂ already becomes an indirect semiconductor under a tensile strain of 1% [13]. After GW correction, both of the G_0W_0 and sc GW_0 QP band structures show that MoS₂ is still a direct semiconductor with K to K band gaps of 2.50 and 2.66 eV, respectively. As the strain increases, shown in Fig. 3(c) and 3(d), the DFT, G_0W_0 and sc GW_0 all predict monolayer MoS₂ to be indirect. The calculated indirect band gaps from DFT, G_0W_0 and sc GW_0 are 1.20 (0.63), 2.19 (1.56), and 2.23 (1.59) for monolayer MoS₂ under strain of 3% (6%),

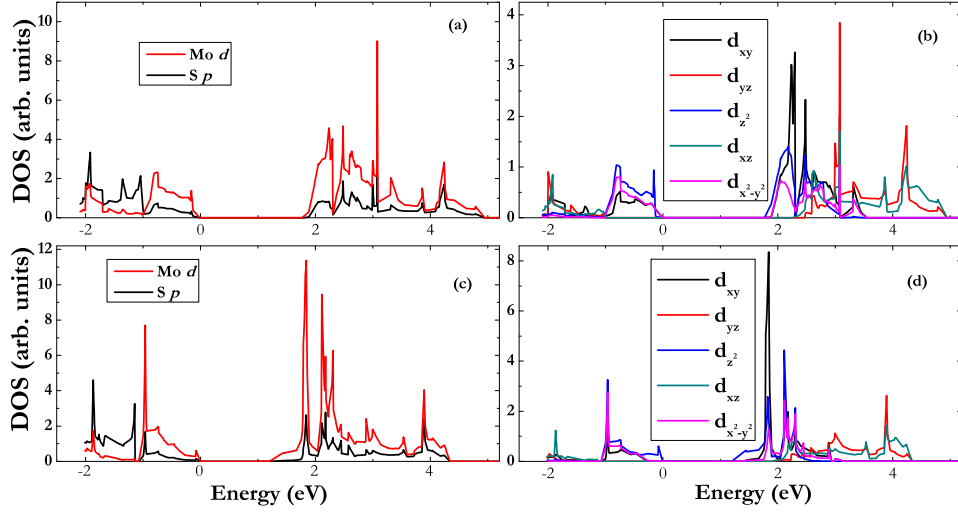


FIG. 1: Projected density of states of d orbitals of Mo (a and c) and p orbitals of S (b and d) and decomposed d orbital of Mo for monolayer MoS₂ at lattice constants of 3.160 (a and b) and 3.255 Å (c and d), respectively. The latter corresponds to 3% strain.

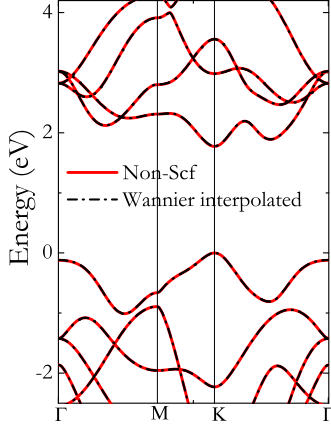


FIG. 2: DFT band structures of monolayer MoS₂ at lattice constant of 3.160 Å obtained by the Non-Scf calculation and Wannier interpolation method.

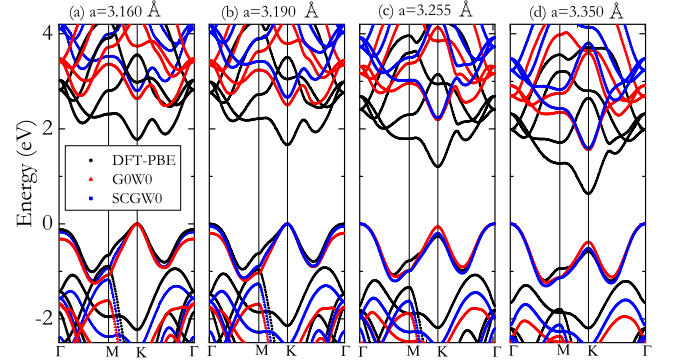


FIG. 3: DFT, G_0W_0 , and $scGW_0$ QP band structures for monolayer MoS₂ at lattice constants of (a) 3.160, (b) 3.190 (the optimized lattice constant from this work), (c) 3.255, and (d) 3.350 Å corresponding to 0%, 1%, 3%, and 6% tensile strain (with reference to 3.160 Å), respectively. The Fermi level is set to be zero.

respectively. As shown in Fig. 3, the value of band gap decreases as the tensile strain increases, accompanying a shift of valence band maximum (VBM) from K to Γ point and resulting in a direct to indirect band gap transition.

To further understand the direct to indirect gap transition and determine this transition point, the band gaps as a function of tensile strain are plotted in Fig. 4. Clearly our DFT and $scGW_0$ results have the same trends, and accord well with reported DFT [13] (cyan triangle) and $scGW$ [24] (green solid square) results, respectively. The inset in Fig. 4 is the energy difference between the valence band top (VBT) at K and Γ points, which determines the direct to indirect gap transition for monolayer MoS₂ under tensile strain. The dependence of the energy difference on the tensile strain is almost linear both for DFT and $scGW_0$ results, and the estimated direct to

indirect transition occurs at about 0.94% and 1.41% for DFT and $scGW_0$, respectively, marked by vertical black and red lines in Fig. 4. The former is consistent well with reported DFT prediction of 1% [13], while a smaller value of 0.3% was obtained in Ref.[10]. The difference originates from the relative position of VBT at K and Γ points mainly due to the pseudopotential and all-electron methods adopted at DFT level and becomes small after GW correction. Above all, our $scGW_0$ predicts a wider range for MoS₂ maintaining its direct gap characteristic compared to DFT results. This direct-indirect band gap transition also indicates that PL of monolayer MoS₂ becomes weaker under tensile tension of 1.41% and above, while corresponding experimental result is still lacking now. The optical gap shown in Fig. 4 will be discussed in the next subsection.

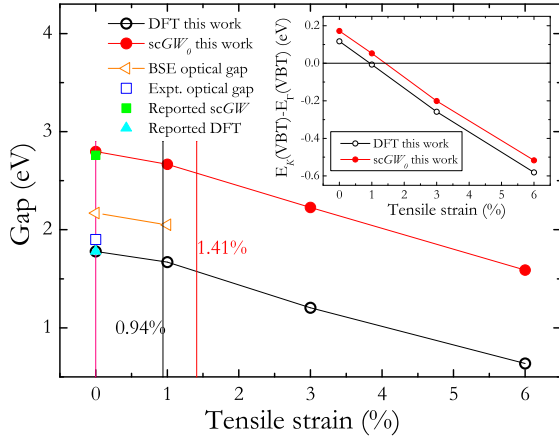


FIG. 4: Band gaps for monolayer MoS₂ obtained by DFT, scGW₀, and BSE. Reported experimental (Expt.) [7], DFT [13], and scGW [24] results are also shown. The inset is the energy difference between the valence band tops at *K* and Γ points.

B. Excitonic effect in monolayer MoS₂

In this subsection, the optical properties of monolayer MoS₂ are discussed in details. From the technical view, optical transition simulation needs the integration over the irreducible Brillouin zone using sufficiently dense *k*-point mesh. Naturally, the convergence of *k*-point sampling is important. First, for monolayer MoS₂ at strainless case (3.16 Å), the optical adsorption spectra ε_2 ($\varepsilon_{xx} = \varepsilon_{yy}$) obtained by different *k*-point meshes are illustrated in Fig. 5(a), in which the independent-particle (IP) picture is adopted within DFT (DFT-IP) and no local field effect is included at hartree or DFT level. The first peak at about 1.78 eV is observed clearly in all the cases, corresponding to the *K*-*K* direct transition. The second significant peak located at about 2.75 eV is converged for 12×12×1 and 15×15×1 *k*-point meshes. Other peaks in adsorption spectra between the two aforementioned dominated peaks mainly originate from different irreducible *k* points with unequal weights in different *k*-point meshes. According to our analysis of projected density of states, the two significant peaks located in 1.78 and 2.75 eV correspond to *d*-*d* and *p*-*d* transitions, respectively. Considering the dipolar selection rule only transitions with the difference $\Delta l = \pm 1$ between the angular momentum quantum numbers *l* are allowed, *i.e.*, the atomic *d*-*d* transition is forbidden. However, in the monolayer MoS₂, due to the orbital hybridization, the VBM and conduction band minimum (CBM) still have *p* orbital contributions, especially the former; thus the VBM to CBM transition dominated by *d*-*d* transition is still allowed. As expected, the strength of this *d*-*d* transition is weaker than the *p*-*d* transition as shown in Fig. 5(a).

As for the BSE calculations, in order to reduce the computational cost, we adopt 400 and 200 eV for the

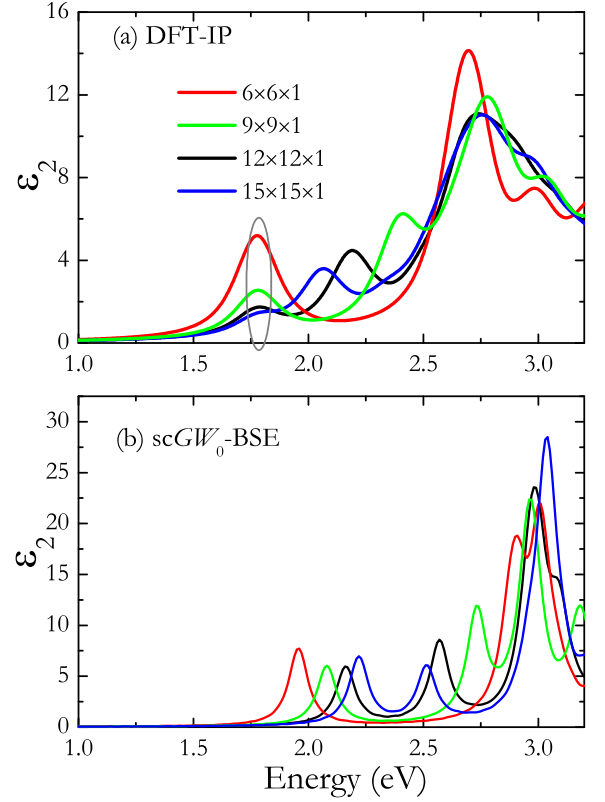


FIG. 5: DFT-IP and scGW₀+BSE adsorption spectra for monolayer MoS₂ at experimental lattice of 3.16 Å (strainless case) obtained by different *k*-point meshes.

plane wave energy cutoff and response function energy cutoff (short for 400 and 200 eV for energy cutoffs), respectively, while the accuracy still can be guaranteed. Taking the strainless monolayer MoS₂ for example, the scGW₀ band gap is 2.78 eV, resulting in only 0.02 eV difference compared to 2.80 eV aforementioned using 600 and 300 eV for energy cutoffs. The calculated BSE spectra for strainless monolayer MoS₂ are plotted in Fig. 5(b). It is clearly that as *k*-point mesh refines, the first peaks have a blueshift. For *k*-point meshes 6×6×1, 9×9×1, 12×12×1, and 15×15×1, the scGW₀ band gaps are 2.99, 2.84, 2.78, and 2.76 eV, respectively; the first adsorption peaks (optical band gaps) are 1.96, 2.08, 2.16, and 2.22 eV. Correspondingly, the exciton binding energies are 1.03, 0.76, 0.62, and 0.54 eV, inferred from the difference between the QP (scGW₀) and optical (scGW₀-BSE) gaps. These calculated QP band gaps, optical gaps and exciton binding energies are also listed in Table I. The convergence trend is obvious, particularly for the electronic band gap. However, due to the limitation of computation resource, scGW₀ calculations with more dense *k*-point mesh are not performed here. Note that previous theoretical results showed a much larger value of exciton binding energy for monolayer MoS₂. For example, a value of 0.9 eV for monolayer MoS₂ (3.16 Å) was obtained using empirical Mott-Wannier theory [24]; and

TABLE I: QP band gap, optical band gap and exciton binding energy for monolayer MoS₂ and WS₂ are obtained by QP $scGW_0$ and BSE with and without spin-orbital coupling (SOC) adopting different energy cutoffs and k -point mesh. All energies are in the unit of eV.

	Energy cutoffs	k -point	E_g	$E_g(\text{optical})$	Binding energy
Monolayer MoS ₂ (3.160 Å)	400 and 200	6×6×1(SOC)	2.89	1.87	1.01
		6×6×1	2.99	1.96	1.03
		9×9×1	2.84	2.08	0.76
		12×12×1	2.78	2.16	0.62
		15×15×1	2.76	2.22	0.54
	600 and 300	12×12×1	2.80	2.17	0.63
Monolayer MoS ₂ (3.190 Å)	600 and 300	12×12×1	2.66	2.04	0.62
Monolayer WS ₂ (3.155 Å)	400 and 200	6×6×1(SOC)	3.02	1.97	1.05
		6×6×1	3.28	2.21	1.07
		9×9×1	3.12	2.34	0.78
		12×12×1	3.06	2.43	0.63
		15×15×1	3.05	2.51	0.54
	600 and 300	12×12×1	3.11	2.46	0.65
Monolayer WS ₂ (3.190 Å)	600 and 300	12×12×1	2.92	2.28	0.64

a value of 1.03 eV was obtained by G_0W_0 -BSE calculations for monolayer MoS₂ (3.18 Å) using 6×6×1 k -point mesh and including spin-orbital coupling [25], which is the same as our above results using the same k -point mesh without spin-orbital coupling. Apparently, these results overestimated the exciton binding energy due to the insufficient k -point mesh in the first-principles calculations.

Experimentally, two close peaks observed in adsorption spectrum of monolayer MoS₂ around 1.9 eV are due to the valence band splitting caused by spin-orbital coupling. In our calculations, the spin-orbital coupling is omitted unless otherwise stated and this will not alter our main conclusions presented in the current study. In order to make a comparison, we also performed the $scGW_0$ -BSE calculations with spin-orbital coupling using 6×6×1 k -point mesh and 400 and 200 eV for energy cutoffs. The two peaks in BSE adsorption spectrum locate at 1.87 and 2.05 eV and the corresponding exciton binding energy is 1.02 eV, consistent well with the aforementioned G_0W_0 -BSE calculations using the same k -point mesh and energy cutoffs while different pseudopotentials [25]. Notice that the exciton binding energy obtained with and without spin-orbital coupling for monolayer MoS₂ as shown in Table I is nearly the same, while the optical gap in the former case shifts about 0.1 eV towards lower energy due to the top valence band splitting of 0.17 eV according to our $scGW_0$ calculation.

Based on our above results and discussions, the exciton binding energy for monolayer MoS₂ is predicted to be in the range of 0.50–0.40 eV, while experimental value is still lacking. For one dimensional system like carbon nanotube (CNT), a similar exciton binding energy of about 0.4 eV was also obtained for semiconducting CNT with

0.8 nm diameters [26–28].

For the evolution of exciton binding energy as a function of strain, our results demonstrate that it is almost unchanged, i.e., 0.63 eV (strainless), 0.62 eV (1% strain), 0.62 eV (3% strain), and 0.59 eV (6% strain) (using 600 and 300 eV for energy cutoffs and 12×12×1 k -point mesh). The direct optical gaps are 2.17, 2.04, 1.81, 1.52 eV for the four cases shown in Fig. 3, respectively. The former two are also shown in Fig. 4 using the orange left triangles. The experimental optical gap for monolayer MoS₂ was shown to be about 1.90 eV [7]. Since there was no mention of specific lattice parameter, here it is assumed to be the strainless case as shown in Fig. 4. Notice that the consistency is good between our theoretical and experimental results. If spin orbital coupling is taken into account, the consistency will be improved further, since the first peak in the adsorption spectrum moves towards lower energy due to the top valence band splitting. Most importantly, our results demonstrate that the optical gap of monolayer MoS₂ is very sensitive to tensile strain, which can be tuned by depositing monolayer MoS₂ on different substrates [14], whereas the exciton binding energy is insensitive to it.

C. Chemical bonding properties of monolayer MoS₂

In order to gain further insight into the electronic structures under the tensile strain, we revisit the DOS shown in Fig. 1. For the strainless case, the VBM states at K mainly originate from d_{xy} and $d_{x^2-y^2}$, while under 3% tensile strain, the VBM states at Γ mainly originate from d_{z^2} . The CBM at K is mainly contributed by d_{z^2} .

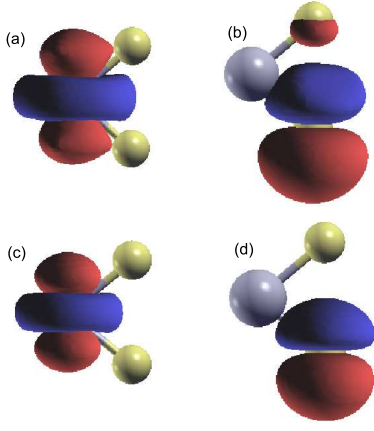


FIG. 6: MLWFs isosurface plots for Mo d_{z^2} (a and c) and S p_z (b and d) for MoS₂ under strainless (a and b) and 3% tensile strain (c and d) cases, respectively.

The top valence bands at Γ point shift upwards compared to those at K point while CBM at K shifts downwards as the strain increases. Clearly under the tensile strain, the hybridization between Mo d and S p becomes weak. MLWFs can also illustrate the chemical bonding properties of solids [29]. MLWFs for Mo d_{z^2} and S p_z in monolayer MoS₂ for both strainless and 3% tensile strain cases are plotted in Fig. 6. It is seen that the overlap of MLWFs for Mo d_{z^2} and S p_z becomes weak due to the strain. In Fig. 6(a), the MLWFs for Mo d_{z^2} have certain degree distortion towards S atom, while this is not observed in Fig. 6(c). As the strain increases, the ionic bond character is increased in monolayer MoS₂. At about 10% tensile strain, according to DFT studies, a semiconductor to metal transition occurs [12, 13].

D. QP band structures and optical properties of strained monolayer WS₂

The QP band structures of monolayer WS₂ under tensile strain are also investigated, motivated by its better performance than monolayer MoS₂ used as a channel in transistor devices [30]. The calculation results are illustrated in Fig. 7. Similar to monolayer MoS₂, the $scGW_0$ QP band structures of monolayer WS₂ also undergo a direct to indirect band gap transition as tensile strain increases. The direct band gaps for the strainless (at the experimental lattice of 3.155 Å [10]) and under 1% tensile strain cases are 3.11 and 2.92 eV, respectively, and the latter corresponds to the optimized lattice constant for monolayer WS₂ from this work. The corresponding indirect band gaps under 3% and 6% tensile strains are 2.49 and 1.78 eV, respectively. Note that for the strainless case, our DFT result predicts monolayer WS₂ to be an indirect band gap semiconductor with CBM only about 16 meV lower than the lowest conduction band at K points, which is contrary to recent full potential methods [10]. The difference may be originated from the

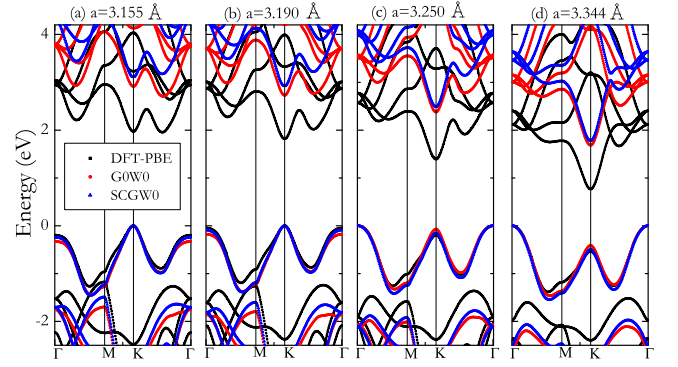


FIG. 7: DFT, G_0W_0 , and $scGW_0$ QP band structures for WS₂ at lattice constants of (a) 3.155, (b) 3.190 (optimized lattice constant this work), (c) 3.250, and (d) 3.344 Å, corresponding to 0%, 1%, 3%, and 6% tensile strain (with reference to 3.155 Å), respectively. The Fermi level is set to be zero.

technical aspect of these calculations, such as the employed pseudopotential method [31]. However, after the GW correction, a correct direct band gap is achieved.

At the GW level, the dependence of energy difference between the VBT at K and Γ point on strain for monolayer WS₂ is similar to that of monolayer MoS₂ as shown in Fig. 4. The direct to indirect transition for monolayer WS₂ is predicted to occur at 1.74% tensile strain by $scGW_0$ calculations.

For optical properties of monolayer WS₂, our calculated QP band gaps, optical gaps and exciton binding energies are also listed in Table I. It is obvious that the monolayer WS₂ presents many similar properties compared to monolayer MoS₂, for example, the gaps and exciton binding energy also demonstrate a convergence trend as k -point mesh increases; the spin orbital coupling has little influence on the magnitude of the exciton binding energy. Notice that our $scGW_0$ calculation predicts the top valence band splitting of monolayer WS₂ to be 0.44 eV, larger than that of monolayer MoS₂ of 0.17 eV, because W is much heavier than Mo. The resulting first peak in BSE adsorption spectrum shifts 0.24 eV towards lower energy, also larger than that of monolayer MoS₂ of 0.1 eV correspondingly. As for the strain effect, the BSE optical gap at our optimized lattice constant of 3.190 Å is 2.28 eV, while at 3.16 Å it is 2.46 eV, as shown in Table I. The former corresponding to 1% tensile strain, results in 0.18 eV reduction of band gaps. This demonstrates that the band gaps and optical gaps are also very sensitive to tensile strain, whereas the exciton binding energy is not. Based on above analysis, we also predict the exciton binding energy for monolayer WS₂ to be in the range of 0.5–0.4 eV, similar to that monolayer MoS₂. Experimentally, the PL maximum of monolayer WS₂ locates between 1.94 and 1.99 eV [32]. Considering the large shift of the peak in the BSE adsorption spectrum caused by spin orbital coupling, our results at optimized lattice of 3.190 Å are consistent well with above experimental result. Notice that the self-consistent GW

TABLE II: Electron and hole effective masses (m^*) derived from partially $scGW_0$ QP band structures for monolayer MoS₂, WS₂, MoSe₂, and WSe₂ at different strains. The effective masses at K and Γ points are along KT and MT directions, respectively.

		Compressive (1%).	Experimental.	Optimized.	Tensile (3%)	Tensile (6%)
MoS ₂	K_e	0.40	0.36 (0.60 ^a , 0.35 ^b)	0.32	0.29	0.27
	K_h	0.40	0.39 (0.54 ^a , 0.44 ^b)	0.37		
	Γ_h				1.36	0.90
WS ₂	K_e		0.27	0.24	0.22	0.20
	K_h		0.32	0.31		
	Γ_h				1.24	0.79
MoSe ₂	K_e		0.38	0.36		
	K_h		0.44	0.42		
WSe ₂	K_e		0.29	0.26		
	K_h		0.34	0.33		

^aEffective masses listed here are averages of the longitudinal and transverse values in Ref. [24].

^bEffective masses listed here are averages of the curvatures along the ΓK and KM directions in Ref. [25]

method with vertex correction in W , which corresponds to the attractive interaction between hole and holes, also yields excellent band gaps [33].

According to our above $scGW_0$ and BSE calculations for monolayer MoS₂ and WS₂, it is clear that the self energy within the $scGW_0$ calculations enlarges the band gap by accounting for the many body electron-electron interactions more accurately, while the strong excitonic effect results in a significant reduction of the band gap. Combining the two opposite effects on band gaps, the final resulting optical gap is consistent well with DFT band gaps. Therefore, the good band gap agreement between DFT and experiment is only a coincidence due to the fact that QP band gap correction is almost offset by exciton binding energy. This phenomenon was also observed in monolayer of hybridized garphene and hexagonal boron nitride, which also have strong excitonic effect [34].

We also perform the $scGW_0$ QP band structures for monolayer MoS₂ and WS₂ under 1% compressive strains. Our results show that the compressed MoS₂ has a direct band gap of 2.97 eV, while the compressed WS₂ has an indirect band gap of 3.13 eV and K to K direct gap of 3.30 eV.

Our $scGW_0$ results show that both MoSe₂ and WSe₂ are also a direct semiconductor at the strainless state. The experimental lattice constants [10] for MoSe₂ and WSe₂ are 3.299 and 3.286 Å and the optimized lattice constants are 3.327 and 3.326 Å, respectively; their direct K - K band gaps are 2.40 and 2.68 eV at experimental lattices and 2.30 and 2.50 eV at the optimized lattices. Compared to the experimental lattice, the optimized lattice corresponds to 0.86% (1.22%) tensile strain for MoSe₂ (WSe₂), and the band gap also decreases with increasing tensile strain.

E. Effective mass

Based on the more accurate $scGW_0$ QP band structures, the effective mass of carriers for TMDs are cal-

culated by fitting the bands to a parabola according to $E = \frac{\hbar^2 k^2}{2m_e m^*}$, where m_e is the electron static mass. A k -point spacing smaller than 0.03 Å⁻¹ is used to keep parabolic effects. Electron and hole effective masses (m^*) at different strains are collected in Table II. For MoS₂ under different strains, the CBM always locates in K point, and the electron effective mass K_e increases with increasing compressive strain while decreases with increasing tensile strain. As for hole, initially the effective mass also decreases as the tensile strain increases. After the direct to indirect gap transition, VBM shifts to Γ with heavier hole, which also decreases as the tensile strain increases. Compared to the effective masses of 0.64 and 0.48 for hole and electron at K point based on DFT calculation performed at the experimental lattice [10] for MoS₂, the effective masses are reduced due to the GW correction in our study. For WS₂, MoSe₂, and WSe₂, their masses also show similar behaviors. It is noted that at the same strain level, the mass of WS₂ is the lightest, making WS₂ more attractive for high performance electronic device applications since a lighter electron effective mass can lead to a higher mobility. Theoretical device simulations also demonstrated that as a channel material, the performance of WS₂ is superior to that of other TMDs [30].

IV. SUMMARY

In summary, the QP band structures of monolayer MoS₂ and WS₂ at both strainless and strained states have been studied systematically. The $scGW_0$ calculations are found to be reliable for such calculations. Using this approach, we find their band structures share many similar behaviors. At strainless state or under a small tensile strain, they maintain their direct band gap characteristics. As the tensile strain increases, they undergo a direct-indirect band gap transition. For the optical properties, exciton binding energy is predicted to

be in the range of 0.50–0.40 eV, which is much smaller than previous results and insensitive to the strains. Our calculated optical band gap is also consistent with experimental results. In addition, we find that the electron effective masses of monolayer MoS₂, WS₂, MoSe₂, and WSe₂ reduce as the tensile strain increases, and WS₂ possesses the lightest mass among the four monolayer materials at the same strain. Importantly, the present work highlights a possible avenue to tune the electronic properties of monolayer TMDs using strain engineering

for potential applications in high performance electronic devices.

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